





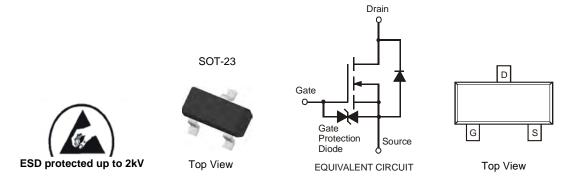
N-CHANNEL ENHANCEMENT MODE MOSFET

Features

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Lead, Halogen and Antimony Free, RoHS Compliant "Green" Device (Notes 1 and 2)
- ESD Protected Up To 2kV
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT-23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin annealed over Alloy 42 leadframe. Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Weight: 0.008 grams (approximate)



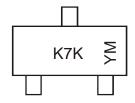
Ordering Information (Note 3)

Part Number	Case	Packaging
2N7002K-7	SOT-23	3000/Tape & Reel

Notes:

- 1. No purposefully added lead. Halogen and Antimony Free.
- 2. Diodes Inc.`s "Green" Policy can be found on our website at http://www.diodes.com
- 3. For packaging details, go to our website at http://www.diodes.com.

Marking Information



K7K = Product Type Marking Code YM = Date Code Marking Y = Year (ex: T = 2006) M = Month (ex: 9 = September)

Date Code Key

Date Code Ite												
Year	200	6	2007		2008	20	09	2010		2011	2	2012
Code	Т		U		V	\	٧	Χ		Υ		Z
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings @TA = 25°C unless otherwise specified

Characteristic	Symbol	Value	Units	
Drain-Source Voltage		V_{DSS}	60	V
Gate-Source Voltage		V_{GSS}	±20	V
Drain Current (Note 4)	Continuous Pulsed (Note 5)	I _D	300 800	mA

Thermal Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Units	
Total Power Dissipation (Note 4)	P_{D}	350	mW	
Thermal Resistance, Junction to Ambient	$R_{ heta JA}$	357	°C/W	
Operating and Storage Temperature Range	T _{J,} T _{STG}	-65 to +150	°C	

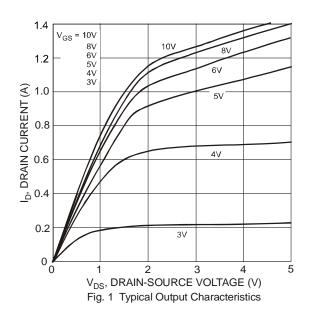
Electrical Characteristics @TA = 25°C unless otherwise specified

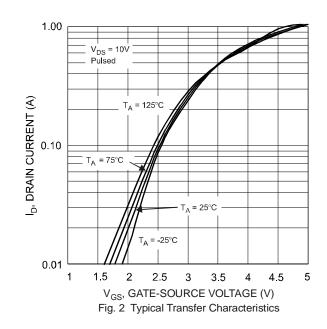
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)				-		
Drain-Source Breakdown Voltage	BV_{DSS}	60		_	V	$V_{GS} = 0V, I_D = 10\mu A$
Zero Gate Voltage Drain Current	I _{DSS}			1.0	μА	$V_{DS} = 60V, V_{GS} = 0V$
Gate-Source Leakage	I _{GSS}	_		±10	μΑ	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 6)						
Gate Threshold Voltage	$V_{GS(th)}$	1.0	1.6	2.5	V	$V_{DS} = 10V, I_D = 1mA$
Static Drain-Source On-Resistance	R _{DS} (ON)	_	_	2.0	Ω	$V_{GS} = 10V, I_D = 0.5A$
Static Dialit-Source Off-Resistance				3.0		$V_{GS} = 5V, I_D = 0.05A$
Forward Transfer Admittance	Y _{fs}	80	_	_	ms	$V_{DS} = 10V, I_D = 0.2A$
DYNAMIC CHARACTERISTICS						
Input Capacitance	C _{iss}	_		50	pF	N/ 05N/ N/ 0N/
Output Capacitance	Coss			25	pF	$V_{DS} = 25V, V_{GS} = 0V$ f = 1.0MHz
Reverse Transfer Capacitance	C _{rss}	_	_	5.0	pF	= 1.0 V Z

Notes: 4. Device mounted on FR-4 PCB.

5. Pulse width ≤10μS, Duty Cycle ≤1%.

^{5.} Short duration pulse test used to minimize self-heating effect.







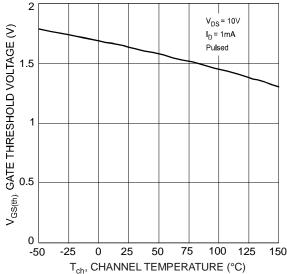


Fig. 3 Gate Threshold Voltage vs. Channel Temperature

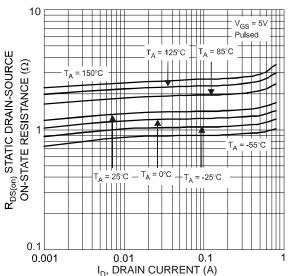


Fig. 5 Static Drain-Source On-Resistance vs. Drain Current

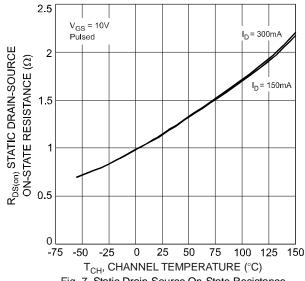


Fig. 7 Static Drain-Source On-State Resistance vs. Channel Temperature

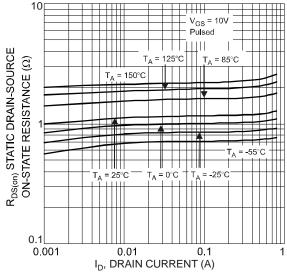


Fig. 4 Static Drain-Source On-Resistance vs. Drain Current

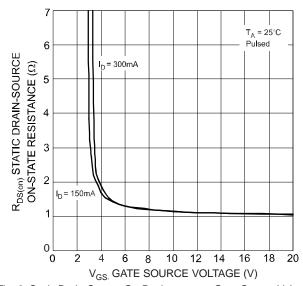
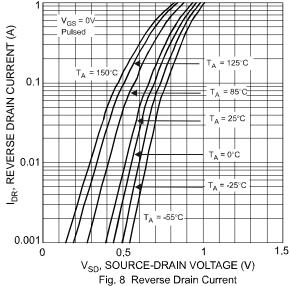


Fig. 6 Static Drain-Source On-Resistance vs. Gate-Source Voltage





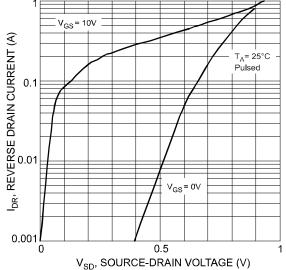
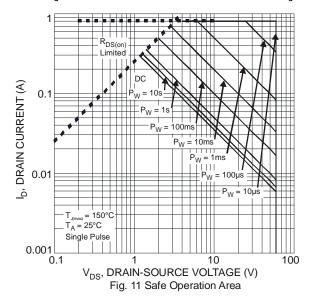


Fig. 9 Reverse Drain Current vs. Source-Drain Voltage



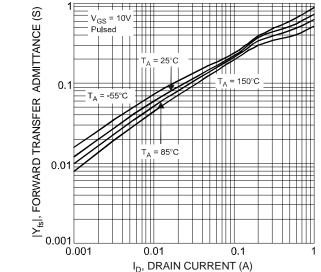
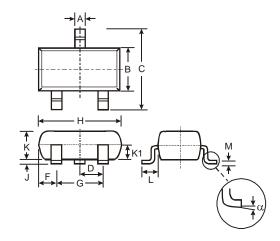


Fig.10 Forward Transfer Admittance vs. Drain Current

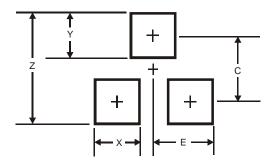
Package Outline Dimensions



SOT23							
Dim	Min	Max	Тур				
Α	0.37	0.51	0.40				
В	1.20	1.40	1.30				
С	2.30	2.50	2.40				
D	0.89	1.03	0.915				
F	0.45	0.60	0.535				
G	1.78	2.05	1.83				
Н	2.80	3.00	2.90				
J	0.013	0.10	0.05				
K	0.903	1.10	1.00				
K1	-	1	0.400				
L	0.45	0.61	0.55				
M	0.085	0.18	0.11				
α	0°	8°	-				
All Dimensions in mm							



Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Υ	0.9
С	2.0
Е	1.35

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